# **BYV26A THRU BYV26E**

### **SUPER FAST RECTIFIERS**

Reverse Voltage - 200 to 1000 V

Forward Current - 1 A

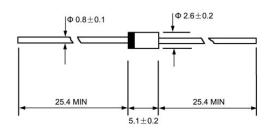
#### **Features**

- Low cost
- Diffused junction
- Low forward voltage drop
- High current capability

### **Mechanical Data**

- Case: Molded plastic, DO-41
- Lead: Axial leads, solderable per MIL-STD-202, Method 208
- Polarity: Color band denotes cathode end
- Mounting Position: Any

### DO - 41



Dimensions in millimeters

## **Maximum Ratings and Electrical Characteristics**

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half-wave, 50 Hz, resistive or inductive load, for capacitive load, derate current by 20%.

Symbols	BYV26A	BYV26B	BYV26C	BYV26D	BYV26E	Units
$V_{RRM}$	200	400	600	800	1000	V
V <sub>RMS</sub>	140	280	420	560	700	V
$V_{DC}$	200	400	600	800	1000	V
I <sub>F(AV)</sub>	1					Α
I <sub>FSM</sub>	30				А	
V <sub>F</sub>	2.5				V	
I <sub>R</sub>	5 150					μΑ
t <sub>rr</sub>	30		75		ns	
СЛ	45		4	40		
$R_{\theta JA}$	100				°C/W	
T <sub>j</sub>	- 55 to + 150				°C	
$T_{stg}$	- 55 to + 150				°C	
	$\begin{array}{c} V_{RRM} \\ V_{RMS} \\ V_{DC} \\ \\ I_{F(AV)} \\ \\ I_{FSM} \\ V_{F} \\ \\ I_{R} \\ \\ t_{rr} \\ \\ C_{J} \\ \\ R_{\theta JA} \\ \\ T_{j} \\ \end{array}$	V <sub>RRM</sub> 200 V <sub>RMS</sub> 140 V <sub>DC</sub> 200 I <sub>F(AV)</sub> I <sub>FSM</sub> V <sub>F</sub> I <sub>R</sub> t <sub>rr</sub> C <sub>J</sub> R <sub>θ,JA</sub> T <sub>j</sub>	V <sub>RRM</sub> 200 400 V <sub>RMS</sub> 140 280 V <sub>DC</sub> 200 400 I <sub>F(AV)</sub> I <sub>FSM</sub> V <sub>F</sub> I <sub>R</sub> 30 C <sub>J</sub> 45 R <sub>θJA</sub> T <sub>j</sub> -	V <sub>RRM</sub> 200         400         600           V <sub>RMS</sub> 140         280         420           V <sub>DC</sub> 200         400         600           I <sub>F(AV)</sub> 1         1           I <sub>FSM</sub> 30         2.5           I <sub>R</sub> 5         150           t <sub>rr</sub> 30         45           R <sub>θJA</sub> 100           T <sub>j</sub> -55 to + 15	V <sub>RRM</sub> 200         400         600         800           V <sub>RMS</sub> 140         280         420         560           V <sub>DC</sub> 200         400         600         800           I <sub>F(AV)</sub> 1         30           V <sub>F</sub> 2.5         5         150           I <sub>rr</sub> 30         7           C <sub>J</sub> 45         4           R <sub>θJA</sub> 100         -55 to + 150	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

 $<sup>^{1)}</sup>$  Reverse recovery test conditions:  $I_F = 0.5$  A,  $I_R = 1$  A,  $I_{rr} = 0.25$  A.



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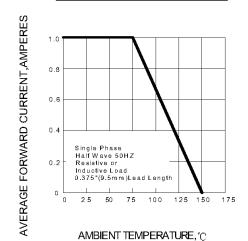




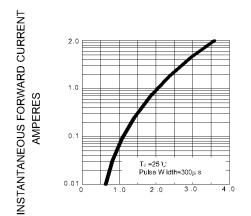
 $<sup>^{\</sup>rm 2)}$  Measured at 1 MHz and applied reverse voltage of 4 V D.C.

<sup>&</sup>lt;sup>3)</sup> Thermal resistance from junction to ambient.

### FIG.1 - FORWARD DERATING CURVE

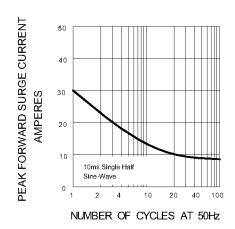


### FIG.2 - TYPICAL FORWARD CHARACTERISTIC

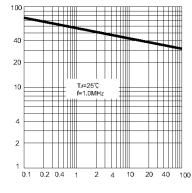


INSTANTANEOUS FORWARD VOLTAGE, VOLTS

### FIG.3 -PEAK FORWARD SURGE CURRENT



### FIG.4 - TYPICAL JUNCTION CAPACITANCE



REVERSE VOLTAGE, VOLTS



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JUNCTION CAPACITANCE, pF







